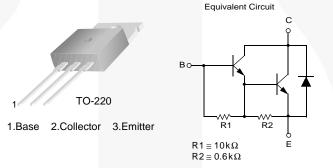


December 2014

TIP102 NPN Epitaxial Silicon Darlington Transistor

Features

- · Monolithic Construction with Built-in Base-Emitter Shunt Resistors
- High DC Current Gain: $h_{FE} = 1000 @ V_{CE} = 4 V$, $I_{C} = 3 A$ (Minimum)
- · Collector-Emitter Sustaining Voltage
- Low Collector-Emitter Saturation Voltage
- Industrial Use
- · Complementary to TIP107



Ordering Information

Part Number	Top Mark	Package	Packing Method
TIP102	TIP102	TO-220 3L (Single Gauge)	Bulk
TIP102TU	TIP102	TO-220 3L (Single Gauge)	Rail

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	100	V
V _{CEO}	Collector-Emitter Voltage	100	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current (DC)	8	Α
I _{CP}	Collector Current (Pulse)	15	Α
I _B	Base Current (DC)	1	Α
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature Range	-65 to 150	°C

Thermal Characteristics

Values are at $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Value	Unit
Pc	Collector Dissipation (T _A = 25°C)		W
r _C	Collector Dissipation (T _C = 25°C)	80	VV

Electrical Characteristics(1)

Values are at $T_C = 25$ °C unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Max.	Unit
V _{CEO} (sus)	Collector-Emitter Sustaining Voltage	$I_C = 30 \text{ mA}, I_B = 0$	100		V
I _{CEO}	Collector Cut-Off Current	$V_{CE} = 50 \text{ V}, I_{B} = 0$		50	μΑ
I _{CBO}	Collector Cut-Off Current	$V_{CB} = 100 \text{ V}, I_{E} = 0$		50	μΑ
I _{EBO}	Emitter Cut-Off Current	$V_{EB} = 5 \text{ V, } I_{C} = 0$		2	mA
h _{FE} [DC Current Gain	$V_{CE} = 4 \text{ V, } I_{C} = 3 \text{ A}$	1000	20000	
		$V_{CE} = 4 \text{ V, } I_{C} = 8 \text{ A}$	200		
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_C = 3 \text{ A}, I_B = 6 \text{ mA}$		2.0	V
		$I_C = 8 \text{ A}, I_B = 80 \text{ mA}$		2.5	V
V _{BE} (on)	Base-Emitter On Voltage	$V_{CE} = 4 \text{ V}, I_{C} = 8 \text{ A}$		2.8	V
C _{ob}	Output Capacitance	V _{CB} = 10 V, I _E = 0, f = 0.1 MHz		200	pF

Note:

1. Pulse test: pw \leq 300 μ s, duty cycle \leq 2%.

Typical Performance Characteristics

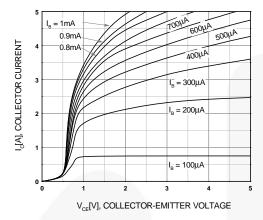


Figure 1. Static Characteristic

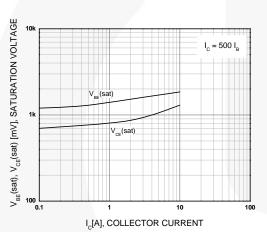


Figure 3. Collector-Emitter Saturation Voltage and Base-Emitter Saturation Voltage

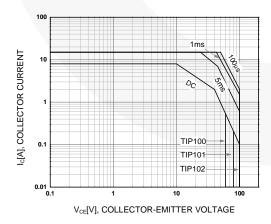


Figure 5. Safe Operating Area

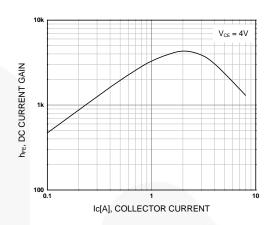


Figure 2. DC Current Gain

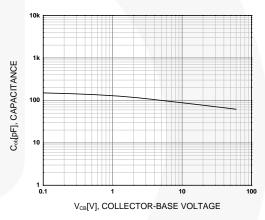


Figure 4. Collector Output Capacitance

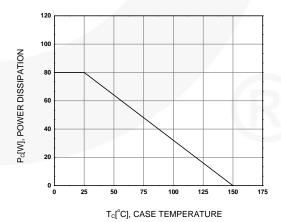
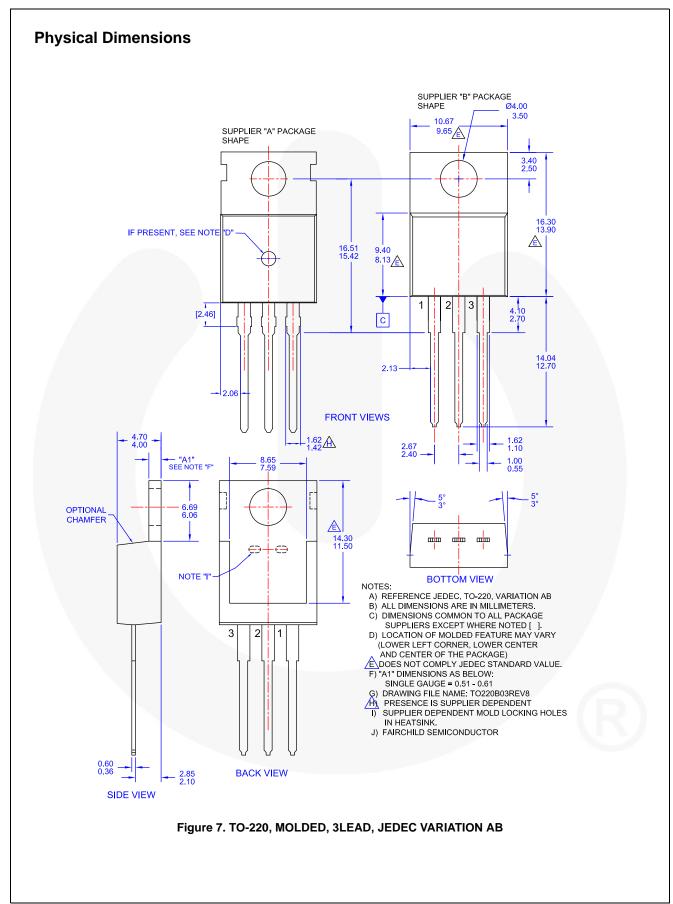


Figure 6. Power Derating







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